

# Magnetic and magnetoresistive properties of CoFe/Au/Co/Au multilayered structures

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In our previous papers [1, 2] we have demonstrated that  $(\text{NiFe}/\text{Au}/\text{Co}/\text{Au})_N$  multilayers (MLs), characterized by in-plane and out-of-plane anisotropy for Ni-Fe and Co layers, respectively, can be applied as magnetoresistive sensors for quantitative measurements of magnetic field. To extend the range of magnetic field corresponding to the linear  $R(H)$  dependence we have replaced Ni-Fe layers by  $\text{Co}_{90}\text{Fe}_{10}$ , *i.e.*, by layers with a larger value of saturation magnetization.

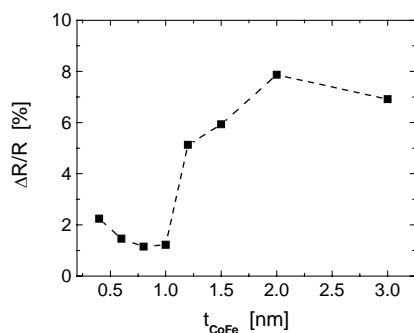


Fig. 1. Amplitude of the GMR effect as a function of  $t_{\text{CoFe}}$ .

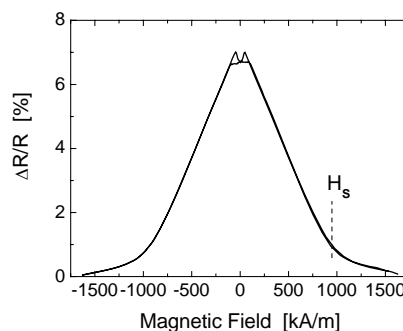


Fig. 2. Magnetoresistance curve for sample with  $t_{\text{CoFe}}=3.0$  nm.

The  $(\text{CoFe-}t_{\text{CoFe}}/\text{Au-2.7}/\text{Co-0.6}/\text{Au-2.7})_{10}$  MLs, with  $t_{\text{CoFe}}$  in the range from 0.4 to 3.0 nm, were deposited by UHV magnetron sputtering. Periodic structure of sample was confirmed by X-ray reflectivity and diffraction. Magnetic reversal and magnetoresistance curves were measured by applying magnetic field both perpendicularly and parallel to the sample plane. For  $t_{\text{CoFe}} \geq 1.2$  nm the  $R(H)$  characteristics are similar to that of the prototype system [1]. However, for smaller  $t_{\text{CoFe}}$  the effective anisotropy of CoFe layers switches from the in-plane anisotropy to the perpendicular one. This transition explains a strong increase of the GMR amplitude between  $t_{\text{CoFe}} = 1$  nm and 1.2 nm (Fig. 1). The relatively large values of GMR amplitude ( $\approx 7\%$ ) and saturation field (900 kA/m) were obtained for sample with  $t_{\text{CoFe}} = 3$  nm, measured in perpendicular field configuration (Fig. 2). The above result indicates a distinct improvement of parameters important for application of studied films as magnetoresistive sensors.

[1] F. Stobiecki *et al.*, J. Magn. Magn. Mater. **282** (2004) 32

[2] B. Szymański *et al.*, J. Alloys Compd. **423** (2006) 236

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